

ABSTRACT OF THE DISCLOSURE

A method ~~of preparing~~ <sup>is provided for preparing, with</sup> ~~in~~ <sup>carbon-doped</sup> high reproducibility, a group III-V compound semiconductor crystal <sup>having</sup> ~~of~~ favorable electrical characteristics ~~with impurities removed~~ <sup>therefrom,</sup> and in which the amount of doped carbon can be adjusted easily <sup>during</sup> ~~in~~ crystal growth ~~is provided.~~ This method ~~of preparing a carbon-doped group III-V compound semiconductor crystal~~ includes the steps of: filling a crucible with compound raw material, solid carbon, and boron oxide; sealing the ~~crucible filled with compound material, solid carbon, and boron oxide~~ within an airtight vessel formed of a gas impermeable material; heating and melting the compound <sup>raw</sup> material under the sealed state in the airtight vessel; and solidifying the melted compound <sup>raw</sup> material to grow a carbon-doped compound semiconductor crystal.